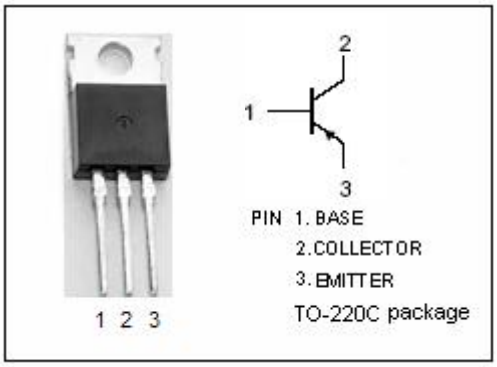
# *isc* Silicon PNP Power Transistor — 2SA1080




## DESCRIPTION

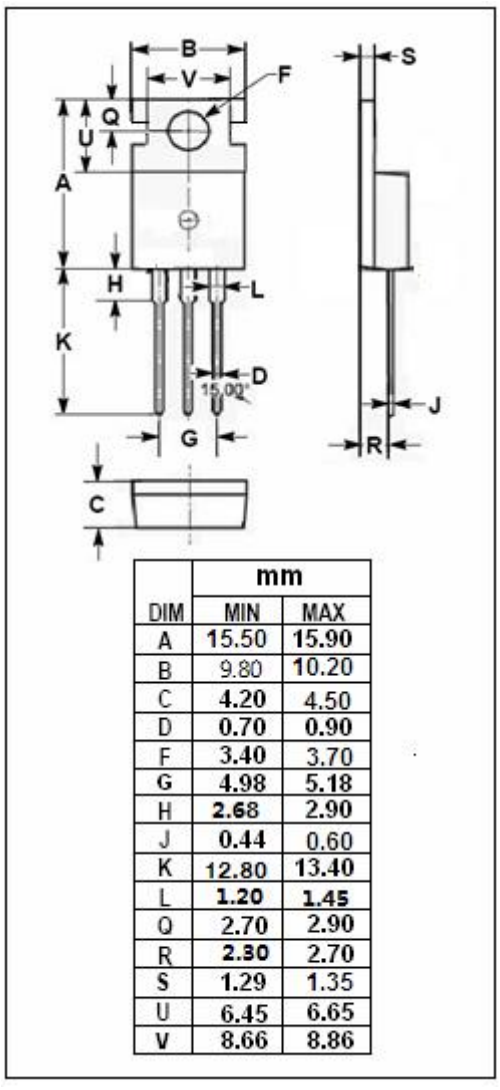
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -40V(Min.)
- Good Linearity of $h_{FE}$
- Complement to Type 2SC2530
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- Designed for medium power amplifier applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|---|---|---|---|
| $V_{CBO}$ | Collector-Base Voltage | -40 | V |
| $V_{CEO}$ | Collector-Emitter Voltage | -40 | V |
| $V_{EBO}$ | Emitter-Base Voltage | -7 | V |
| $I_C$ | Collector Current-Continuous | -0.5 | A |
| $P_C$ | Collector Power Dissipation @$T_C$=25℃ | 20 | W |
| $T_J$ | Junction Temperature | 150 | ℃ |
| $T_{stg}$ | Storage Temperature Range | -65~150 | ℃ |




| DIM | mm MIN | MAX |
|---|---|---|
| A | 15.50 | 15.90 |
| B | 9.80 | 10.20 |
| C | 4.20 | 4.50 |
| D | 0.70 | 0.90 |
| F | 3.40 | 3.70 |
| G | 4.98 | 5.18 |
| H | 2.68 | 2.90 |
| J | 0.44 | 0.60 |
| K | 12.80 | 13.40 |
| L | 1.20 | 1.45 |
| Q | 2.70 | 2.90 |
| R | 2.30 | 2.70 |
| S | 1.29 | 1.35 |
| U | 6.45 | 6.65 |
| V | 8.66 | 8.86 |

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## ELECTRICAL CHARACTERISTICS

**$T_C$=25℃ unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | $I_C$= -1mA; $R_{BE}$= ∞ | -40 | | | V |
| $V_{(BR)CBO}$ | Collector-Base Breakdown Voltage | $I_C$= -0.1 μA; $I_E$= 0 | -40 | | | V |
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | $I_E$= -0.1 μA; $I_C$= 0 | -7 | | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C$= -10mA; $I_B$= -1mA | | | -0.5 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C$= -10mA; $I_B$= -1mA | | | -1.0 | V |
| $I_{CBO}$ | Collector Cutoff Current | $V_{CB}$= -40V; $I_E$= 0 | | | -100 | nA |
| $I_{CEO}$ | Collector Cutoff Current | $V_{CE}$= -40V; $I_B$= 0 | | | -500 | nA |
| $I_{EBO}$ | Emitter Cutoff Current | $V_{EB}$= -7V; $I_C$= 0 | | | -100 | nA |
| $h_{FE}$ | DC Current Gain | $I_C$= -10mA; $V_{CE}$= -5V | 100 | | 350 | |
| $C_{OB}$ | Outut Capacitance | $I_E$= 0; $V_{CB}$= -20V; f= 1.0MHz | | 65 | | pF |
| $f_T$ | Current-Gain—Bandwidth Product | $I_C$= -10mA;$V_{CE}$= -10V; f=10MHz | | 30 | | MHz |